PSMN041-80YL

N-channel 80 V 41 m Ω logic level MOSFET in LFPAK56 Product data sheet

1. **General description**

Logic level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in LFPAK56 package. This product has been designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. **Features and benefits**

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive
- LFPAK56 package is footprint compatible with other Power-SO8 types
- Qualified to 175 °C

Applications 3.

- DC-to-DC converters
- Load switch
- TV power supplies

Quick reference data 4.

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V	
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	-	25	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	64	W	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>		-	32.8	41	mΩ	
resistance	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12		-	-	103	mΩ	
Dynamic chara	Dynamic characteristics							
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 5 A; V _{DS} = 64 V;		-	4.3	-	nC	
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	21.9	-	nC	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 25 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; unclamped; Fig. 3		-	-	23.9	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source		
3	S	source	[d]	G T A
4	G	gate	<u> </u>	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

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Type number	Package					
	Name	Description	Version			
PSMN041-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN041-80YL	04180

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	18	А
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Symbol	Parameter	Conditions	Min	Max	Unit
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	25	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; Fig. 4	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	64	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	54	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	100	Α
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 25 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; unclamped; Fig. 3	-	23.9	mJ

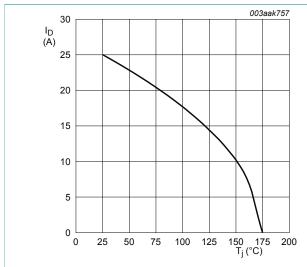


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

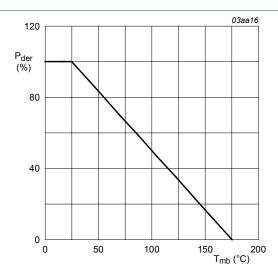


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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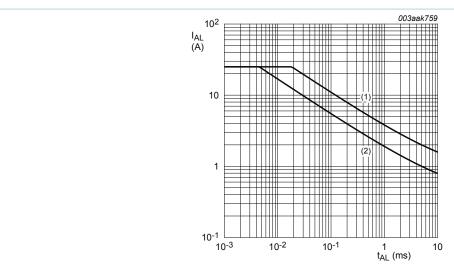
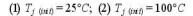


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



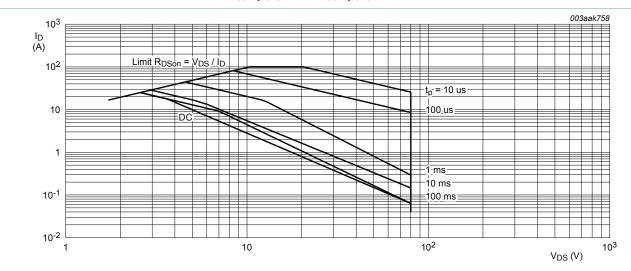


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse

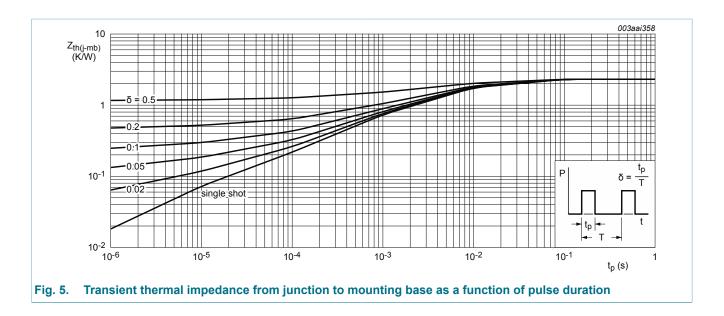
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	2.13	2.33	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	72	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	1.4	1.7	2.1	V	
I _{DSS} dr	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.02	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	32.8	41	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	113	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 13</u> ; <u>Fig. 12</u>	-	-	103	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	35.7	45	mΩ
R_{G}	gate resistance	f = 1 MHz	-	2.02	-	Ω

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 64 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	21.9	-	nC
		I _D = 5 A; V _{DS} = 64 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	11.9	-	nC
Q_{GS}	gate-source charge	I _D = 5 A; V _{DS} = 64 V; V _{GS} = 10 V;	-	2.5	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	1.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	0.8	-	nC
Q_{GD}	gate-drain charge		-	4.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 5 A; V _{DS} = 64 V; T _j = 25 °C; Fig. 14; Fig. 15	-	2.4	-	V
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$	-	1180	-	pF
Coss	output capacitance		-	99	-	pF
C _{rss}	reverse transfer capacitance		-	54	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R_{L} = 10 Ω ; V_{GS} = 5 V;	-	8.6	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	11.2	-	ns
t _{d(off)}	turn-off delay time		-	16.1	-	ns
t _f	fall time		-	10.5	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	21.3	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	22	-	nC

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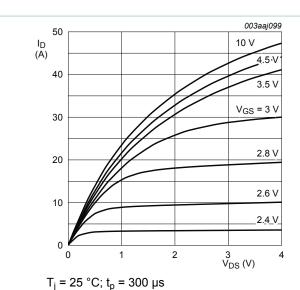


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

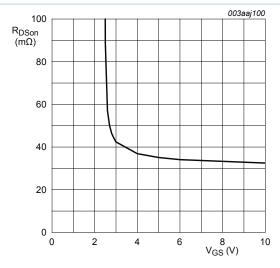


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 5A$

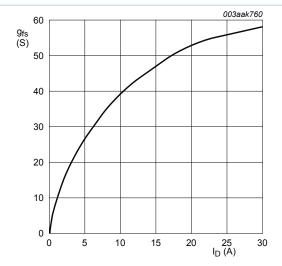


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25$$
°C; $V_{DS} = 10V$

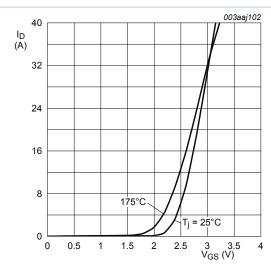


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

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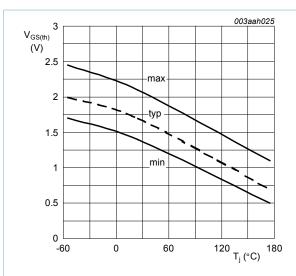


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

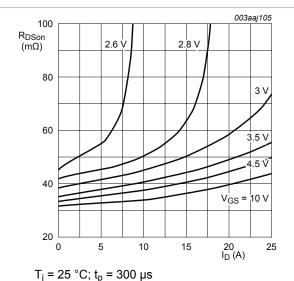


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

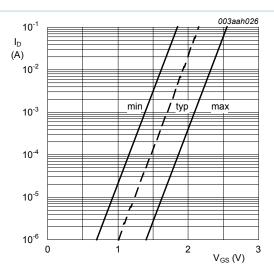


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

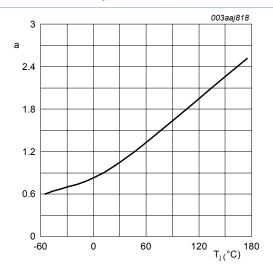


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon} \cos \alpha}$$

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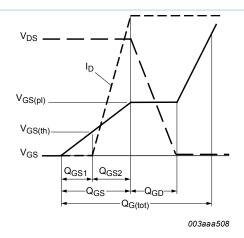


Fig. 14. Gate charge waveform definitions

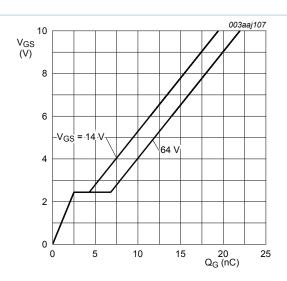


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

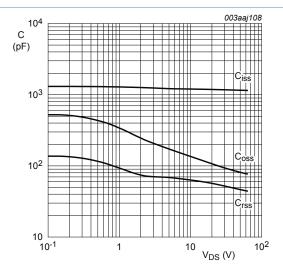


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

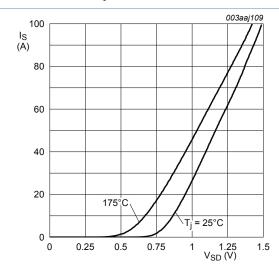


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

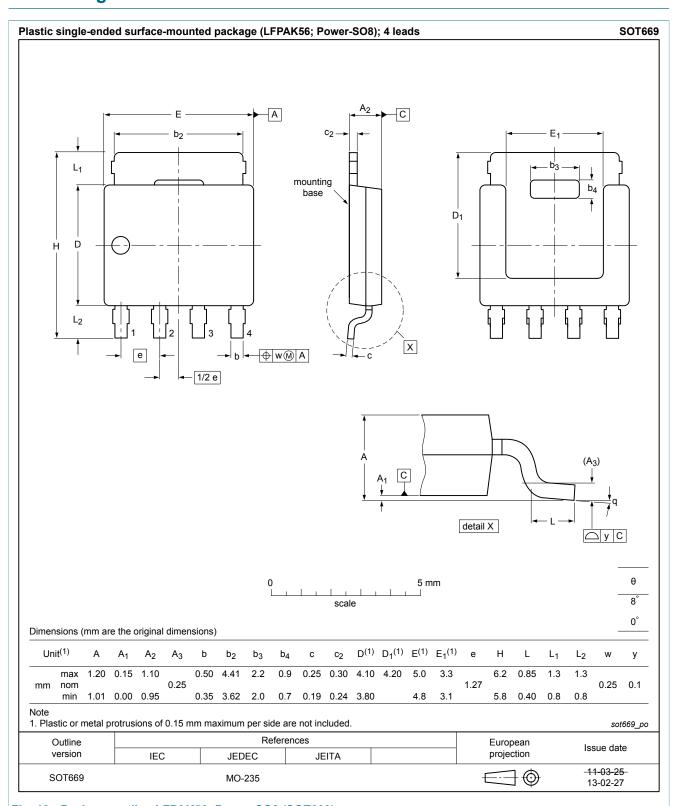


Fig. 18. Package outline LFPAK56; Power-SO8 (SOT669)

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